Paul Fons

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/6137797/publications.pdf

Version: 2024-02-01

341 papers	10,732 citations	31949 53 h-index	43868 91 g-index
348 all docs	348 docs citations	348 times ranked	7099 citing authors

#	Article	IF	Citations
1	Understanding the phase-change mechanism of rewritable optical media. Nature Materials, 2004, 3, 703-708.	13.3	1,193
2	Interfacial phase-change memory. Nature Nanotechnology, 2011, 6, 501-505.	15.6	630
3	ZnO transparent conducting films deposited by pulsed laser deposition for solar cell applications. Thin Solid Films, 2003, 431-432, 369-372.	0.8	237
4	Toward the Ultimate Limit of Phase Change in Ge₂Sb₂Te₅. Nano Letters, 2010, 10, 414-419.	4.5	226
5	Uniaxial locked epitaxy of ZnO on the a face of sapphire. Applied Physics Letters, 2000, 77, 1801.	1.5	192
6	Distortion-triggered loss of long-range order in solids with bonding energy hierarchy. Nature Chemistry, 2011, 3, 311-316.	6.6	178
7	Growth of high-quality epitaxial ZnO films on Î±-Al2O3. Journal of Crystal Growth, 1999, 201-202, 627-632.	0.7	173
8	Raman scattering study of GeTe and Ge2Sb2Te5 phase-change materials. Journal of Physics and Chemistry of Solids, 2007, 68, 1074-1078.	1.9	164
9	Ferroelectric Order Control of the Diracâ€Semimetal Phase in GeTeâ€Sb₂Te₃ Superlattices. Advanced Materials Interfaces, 2014, 1, 1300027.	1.9	155
10	Nitrogen-induced defects in ZnO:N grown on sapphire substrate by gas source MBE. Journal of Crystal Growth, 2000, 209, 526-531.	0.7	152
11	Na-induced variations in the structural, optical, and electrical properties of Cu(In,Ga)Se2 thin films. Journal of Applied Physics, 2009, 106, .	1.1	148
12	Interactions between gallium and nitrogen dopants in ZnO films grown by radical-source molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 4139-4141.	1.5	132
13	Band-gap modified Al-doped Zn1â^'xMgxO transparent conducting films deposited by pulsed laser deposition. Applied Physics Letters, 2004, 85, 1374-1376.	1.5	131
14	Polarization-induced two-dimensional electron gases in ZnMgO/ZnO heterostructures. Applied Physics Letters, 2008, 93, .	1.5	131
15	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. Physical Review Letters, 2006, 96, 045504.	2.9	119
16	Two-dimensional electron gas in Zn polar ZnMgOâ•ZnO heterostructures grown by radical source molecular beam epitaxy. Applied Physics Letters, 2006, 89, 132113.	1.5	118
17	ZnO growth on Si by radical source MBE. Journal of Crystal Growth, 2000, 214-215, 50-54.	0.7	116
18	Band gap energies of bulk, thin-film, and epitaxial layers of CuInSe2 and CuGaSe2. Journal of Applied Physics, 1998, 83, 3678-3689.	1.1	115

#	Article	IF	Citations
19	Local structure of crystallized GeTe films. Applied Physics Letters, 2003, 82, 382-384.	1.5	114
20	Intrinsic complexity of the melt-quenched amorphous Ge<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>Sb<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow	1.1	109
21	Fabrication of wide-gap Cu(In1â^'xGax)Se2 thin film solar cells: a study on the correlation of cell performance with highly resistive i-ZnO layer thickness. Solar Energy Materials and Solar Cells, 2005, 87, 541-548.	3.0	108
22	Pressure-Induced Site-Selective Disordering ofGe2Sb2Te5: A New Insight into Phase-Change Optical Recording. Physical Review Letters, 2006, 97, 035701.	2.9	100
23	Phase transition in crystalline GeTe: Pitfalls of averaging effects. Physical Review B, 2010, 82, .	1.1	95
24	Uniaxial locked growth of high-quality epitaxial ZnO films on -Al2O3. Journal of Crystal Growth, 2000, 209, 532-536.	0.7	85
25	Growth of Undoped ZnO Films with Improved Electrical Properties by Radical Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, 250-254.	0.8	85
26	Photoassisted amorphization of the phase-change memory alloy<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Ge</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msu Physical Review B, 2010, 82, .	1.1	80
27	[illegible] four-electron bonds in GeTe-Sb<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Te<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>phase-change memory alloys. Physical Review B, 2013, 87, .	1.1	76
28	Electrical-field induced giant magnetoresistivity in (non-magnetic) phase change films. Applied Physics Letters, 2011, 99, 152105.	1.5	74
29	Giant multiferroic effects in topological GeTe-Sb₂Te₃superlattices. Science and Technology of Advanced Materials, 2015, 16, 014402.	2.8	73
30	Alkali incorporation control in Cu(In,Ga)Se2 thin films using silicate thin layers and applications in enhancing flexible solar cell efficiency. Applied Physics Letters, 2008, 93, .	1.5	71
31	Role of Ge Switch in Phase Transition: Approach using Atomically Controlled GeTe/Sb₂Te₃ Superlattice. Japanese Journal of Applied Physics, 2008, 47, 5763.	0.8	68
32	Ferroelectric switching in epitaxial GeTe films. APL Materials, 2014, 2, .	2.2	67
33	Effects of the surface Cu2â^'xSe phase on the growth and properties of CuInSe2 films. Applied Physics Letters, 1999, 74, 1630-1632.	1.5	66
34	Molecular dynamics simulations of lowâ€energy particle bombardment effects during vaporâ€phase crystal growth: 10 eV Si atoms incident on Si(001)2Ã—1 surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 3726-3735.	0.9	65
35	Degenerate layers in epitaxial ZnO films grown on sapphire substrates. Applied Physics Letters, 2004, 84, 4412-4414.	1.5	65
36	Heteroepitaxy and characterization of CuInSe2 on GaAs(001). Journal of Crystal Growth, 1995, 150, 1201-1205.	0.7	64

#	Article	IF	Citations
37	Determination of crystallographic polarity of ZnO layers. Applied Physics Letters, 2005, 87, 141904.	1.5	63
38	The order-disorder transition in GeTe: Views from different length-scales. Applied Physics Letters, 2011, 99, .	1.5	63
39	Femtosecond structural transformation of phase-change materials far from equilibrium monitored by coherent phonons. Nature Communications, 2015, 6, 8367.	5.8	62
40	Structural tuning of wide-gap chalcopyrite CuGaSe₂ thin films and highly efficient solar cells: differences from narrow-gap Cu(In,Ga)Se₂. Progress in Photovoltaics: Research and Applications, 2014, 22, 821-829.	4.4	61
41	Selfâ€organized van der Waals epitaxy of layered chalcogenide structures. Physica Status Solidi (B): Basic Research, 2015, 252, 2151-2158.	0.7	61
42	Improved External Efficiency InGaN-Based Light-Emitting Diodes with Transparent Conductive Ga-Doped ZnO as p-Electrodes. Japanese Journal of Applied Physics, 2004, 43, L180-L182.	0.8	59
43	Crystallization-induced short-range order changes in amorphous GeTe. Journal of Physics Condensed Matter, 2004, 16, S5103-S5108.	0.7	58
44	Atomic Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/Sb₂Te₃ Superlattices. ACS Omega, 2017, 2, 6223-6232.	1.6	58
45	In situ diagnostic methods for thin-film fabrication: utilization of heat radiation and light scattering. Progress in Photovoltaics: Research and Applications, 2004, 12, 219-234.	4.4	57
46	Improvement of ZnO TCO film growth for photovoltaic devices by reactive plasma deposition (RPD). Thin Solid Films, 2005, 480-481, 199-203.	0.8	57
47	Mirror-symmetric Magneto-optical Kerr Rotation using Visible Light in [(GeTe)2(Sb2Te3)1]n Topological Superlattices. Scientific Reports, 2014, 4, 5727.	1.6	57
48	Enhanced crystallization of GeTe from an Sb2Te3 template. Applied Physics Letters, 2012, 100, .	1.5	56
49	Why Phase-Change Media Are Fast and Stable: A New Approach to an Old Problem. Japanese Journal of Applied Physics, 2005, 44, 3345-3349.	0.8	55
50	Strong excitonic transition of Zn1â^'xMgxO alloy. Applied Physics Letters, 2007, 91, .	1.5	55
51	Changes in Electronic Structure and Chemical Bonding upon Crystallization of the Phase Change Material<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>GeSb</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Te</mml:mi><mml:mi> Physical Review Letters, 2008, 100, 016402.	2.9	55
52	Growth of N-doped and Ga+N-codoped ZnO films by radical source molecular beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 503-508.	0.7	54
53	Excitonic emissions from CuInSe2 on GaAs(001) grown by molecular beam epitaxy. Applied Physics Letters, 1995, 67, 1289-1291.	1.5	53
54	Development of high-efficiency flexible Cu(In,Ga)Se2 solar cells: A study of alkali doping effects on CIS, CIGS, and CGS using alkali-silicate glass thin layers. Current Applied Physics, 2010, 10, S154-S156.	1.1	53

#	Article	IF	Citations
55	Room-temperature deposition of Al-doped ZnO films by oxygen radical-assisted pulsed laser deposition. Thin Solid Films, 2002, 422, 176-179.	0.8	52
56	Molecular dynamics and quasidynamics simulations of the annealing of bulk and nearâ€surface interstitials formed in molecularâ€beam epitaxial Si due to lowâ€energy particle bombardment during deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 91-97.	0.9	51
57	Growth and electrical properties of ZnO thin films deposited by novel ion plating method. Thin Solid Films, 2003, 445, 274-277.	0.8	51
58	Initial Structure Memory of Pressure-Induced Changes in the Phase-Change Memory Alloy<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Ge</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Sb</mml:mi><mml:mn> Physical Review Letters, 2009, 103, 115502.	2.9	51
59	Instability and Spontaneous Reconstruction of Few-Monolayer Thick GaN Graphitic Structures. Nano Letters, 2016, 16, 4849-4856.	4.5	51
60	High quality CuInSe2 films grown on pseudoâ€latticeâ€matched substrates by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 647-649.	1.5	48
61	What is the Origin of Activation Energy in Phase-Change Film?. Japanese Journal of Applied Physics, 2009, 48, 03A053.	0.8	48
62	Electronic excitation-induced semiconductor-to-metal transition in monolayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>MoTe</mml:mi><mml:mn>2</mml:mn></mml:msub></m Physical Review B, 2016, 94, .	3.1	48
63	Local structure of Ge nanoislands on Si(111) surfaces with a SiO2 coverage. Applied Physics Letters, 2001, 78, 2563-2565.	1.5	47
64	A Sensitive Multilayered Structure Suitable for Biosensing on the BioDVD Platform. Analytical Chemistry, 2009, 81, 4963-4970.	3.2	47
65	Understanding Phase-Change Memory Alloys from a Chemical Perspective. Scientific Reports, 2015, 5, 13698.	1.6	47
66	A two-step process for growth of highly oriented Sb2Te3 using sputtering. AIP Advances, 2016, 6, .	0.6	47
67	Cu(In1â^'xGax)Se2 growth studies by in situ spectroscopic light scattering. Applied Physics Letters, 2003, 82, 2091-2093.	1.5	43
68	Measurements of Temperature Dependence of Optical and Thermal Properties of Optical Disk Materials. Japanese Journal of Applied Physics, 2006, 45, 1419-1421.	0.8	43
69	Improvement of Electrical Properties in ZnO Thin Films Grown by Radical Source(RS)-MBE. Physica Status Solidi A, 2000, 180, 287-292.	1.7	41
70	Epitaxial growth of ZnO thin films on LiNbO3 substrates. Thin Solid Films, 1999, 347, 238-240.	0.8	40
71	Measurement of the thermal conductivity of nanometer scale thin films by thermoreflectance phenomenon. Microelectronic Engineering, 2007, 84, 1792-1796.	1.1	40
72	Temperature Dependence of the Thermal Properties of Optical Memory Materials. Japanese Journal of Applied Physics, 2007, 46, 3909-3911.	0.8	39

#	Article	IF	Citations
73	Similarities and Critical Differences in Heavy Alkali-Metal Rubidium and Cesium Effects on Chalcopyrite Cu(In,Ga)Se₂ Thin-Film Solar Cells. Journal of Physical Chemistry C, 2019, 123, 17757-17764.	1.5	39
74	Effect of band offset on the open circuit voltage of heterojunction CuIn1â^'xGaxSe2 solar cells. Applied Physics Letters, 2004, 85, 5607-5609.	1.5	38
75	Flexible Cu(In,Ga)Se2 solar cells fabricated using alkali-silicate glass thin layers as an alkali source material. Journal of Renewable and Sustainable Energy, 2009, 1, 013102.	0.8	38
76	Terahertz spectroscopic characterization of Ge₂Sb₂Te₅ phase change materials for photonics applications. Journal of Materials Chemistry C, 2019, 7, 8209-8215.	2.7	38
77	On a thermally induced readout mechanism in super-resolution optical disks. Journal of Applied Physics, 2006, 100, 043106.	1.1	37
78	Origin of resistivity contrast in interfacial phase-change memory: The crucial role of Ge/Sb intermixing. Applied Physics Letters, 2019, 114, .	1.5	37
79	Band-edge photoluminescence of CuGaSe2 films grown by molecular beam epitaxy. Journal of Applied Physics, 1996, 79, 4318.	1.1	36
80	A shallow state in molecular beam epitaxial grown CuGaSe2film detectable by 1.62 eV photoluminescence. Journal of Applied Physics, 1997, 81, 2794-2798.	1.1	36
81	Texture and morphology variations in (In,Ga)₂Se₃ and Cu(In,Ga)Se₂ thin films grown with various Se source conditions. Progress in Photovoltaics: Research and Applications, 2013, 21, 544-553.	4.4	36
82	Growth and characterization of undoped ZnO films for single crystal based device use by radical source molecular beam epitaxy (RS-MBE). Journal of Crystal Growth, 2001, 227-228, 923-928.	0.7	35
83	Pressure-induced amorphization of quasibinary GeTeâ€“Sb2Te3: The role of vacancies. Applied Physics Letters, 2007, 91, 021911.	1.5	35
84	Local instability of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>p</mml:mi></mml:math>-type bonding makes amorphous GeTe a lone-pair semiconductor. Physical Review B, 2013, 87, .	1.1	35
85	Electrical properties of Si(100) films doped with lowâ€energy (â‰150 eV) Sb ions during growth by molecular beam epitaxy. Applied Physics Letters, 1988, 53, 1732-1734.	1.5	34
86	Ge L3-edge x-ray absorption near-edge structure study of structural changes accompanying conductivity drift in the amorphous phase of Ge2Sb2Te5. Journal of Applied Physics, 2014, 115, .	1.1	34
87	The effects of thermal treatments on the electrical properties of phosphorus doped ZnO layers grown by MBE. Journal of Crystal Growth, 2005, 278, 268-272.	0.7	33
88	High electron mobility Zn polar ZnMgO/ZnO heterostructures grown by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 358-361.	0.7	33
89	Non-melting super-resolution near-field apertures in Sbâ€“Te alloys. Applied Physics Letters, 2010, 97, 161906.	1.5	33
90	Bandgap Engineering of ZnO Using Se. Physica Status Solidi (B): Basic Research, 2002, 229, 887-890.	0.7	32

#	Article	IF	Citations
91	Growth of ZnO and device applications. Applied Surface Science, 2005, 244, 504-510.	3.1	32
92	Temperature independence of pressure-induced amorphization of the phase-change memory alloy Ge2Sb2Te5. Applied Physics Letters, 2008, 93, .	1.5	32
93	Epitaxy of Geâ€“Sbâ€“Te phase-change memory alloys. Applied Physics Letters, 2009, 94, .	1.5	32
94	Band profiles of ZnMgO/ZnO heterostructures confirmed by Kelvin probe force microscopy. Applied Physics Letters, 2009, 94, .	1.5	32
95	Existence of tetrahedral site symmetry about Ge atoms in a single-crystal film of Ge2Sb2Te5 found by x-ray fluorescence holography. Applied Physics Letters, 2007, 90, 131913.	1.5	31
96	Anion vacancies in CuInSe2. Thin Solid Films, 2001, 387, 129-134.	0.8	30
97	Properties of CuInGaSe2 solar cells based upon an improved three-stage process. Thin Solid Films, 2003, 431-432, 6-10.	0.8	30
98	Growth of polycrystalline Cu(In,Ga)Se2 thin films using a radio frequency-cracked Se-radical beam source and application for photovoltaic devices. Applied Physics Letters, 2007, 91, .	1.5	29
99	Epitaxial phaseâ€change materials. Physica Status Solidi - Rapid Research Letters, 2012, 6, 415-417.	1.2	29
100	Abâ€initio calculations and structural studies of (SiTe) 2 (Sb 2 Te 3) n (n : 1, 2, 4 and 6) phaseâ€change superlattice films. Physica Status Solidi - Rapid Research Letters, 2014, 8, 302-306.	1.2	29
101	Sub-nanometre resolution of atomic motion during electronic excitation in phase-change materials. Scientific Reports, 2016, 6, 20633.	1.6	29
102	Why DVDs work the way they do: The nanometer-scale mechanism of phase change in Geâ€“Sbâ€“Te alloys. Journal of Non-Crystalline Solids, 2006, 352, 1612-1615.	1.5	28
103	Crystalline GeTe-based phase-change alloys: Disorder in order. Physical Review B, 2012, 86, .	1.1	28
104	Selective detection of tetrahedral units in amorphous GeTe-based phase change alloys using Ge L3-edge x-ray absorption near-edge structure spectroscopy. Applied Physics Letters, 2013, 102, 111904.	1.5	28
105	Liquid Ge2Sb2Te5 studied by extended x-ray absorption. Applied Physics Letters, 2009, 95, .	1.5	27
106	Buried p-n junction formation in CuGaSe₂ thin-film solar cells. Applied Physics Letters, 2014, 104, 031606.	1.5	27
107	Excitation-Assisted Disordering of GeTe and Related Solids with Resonant Bonding. Journal of Physical Chemistry C, 2014, 118, 10248-10253.	1.5	27
108	Cr-Triggered Local Structural Change in Cr₂Ge₂Te₆ Phase Change Material. ACS Applied Materials & Interfaces, 2019, 11, 43320-43329.	4.0	26

#	Article	IF	Citations
109	An EXAFS and XANES study of MBE grown Cu-doped ZnO. Nuclear Instruments & Methods in Physics Research B, 2003, 199, 190-194.	0.6	25
110	Doping properties of ZnO thin films for photovoltaic devices grown by URT-IP (ion plating) method. Thin Solid Films, 2004, 451-452, 219-223.	0.8	25
111	Local structure of nitrogen in N-doped amorphous and crystalline GeTe. Applied Physics Letters, 2012, 100, .	1.5	25
112	A hard X-ray nanospectroscopy station at SPring-8 BL39XU. Journal of Physics: Conference Series, 2013, 430, 012017.	0.3	25
113	Effects of RbF postdeposition treatment and heat-light soaking on the metastable acceptor activation of CuInSe2 thin film photovoltaic devices. Applied Physics Letters, 2018, 113, .	1.5	25
114	Photoluminescence properties of sodium incorporation in CuInSe2 and CuIn3Se5 thin films. Solar Energy Materials and Solar Cells, 2001, 67, 289-295.	3.0	24
115	Large grain Cu(In,Ga)Se2 thin film growth using a Se-radical beam source. Solar Energy Materials and Solar Cells, 2009, 93, 792-796.	3.0	24
116	Impact of a binary Ga2Se3 precursor on ternary CuGaSe2 thin-film and solar cell device properties. Applied Physics Letters, 2013, 103, .	1.5	24
117	A Magnetoresistance Induced by a Nonzero Berry Phase in GeTe/Sb 2 Te 3 Chalcogenide Superlattices. Advanced Functional Materials, 2017, 27, 1702243.	7.8	24
118	Electronic Structure of Transition-Metal Based Cu₂GeTe₃ Phase Change Material: Revealing the Key Role of Cu d Electrons. Chemistry of Materials, 2017, 29, 7440-7449.	3.2	24
119	Direct observation of the Cu2â^'xSe phase of Cu-rich epitaxial CuInSe2 grown on GaAs (001). Journal of Applied Physics, 1998, 84, 6926-6928.	1.1	23
120	Optical characterizations of CuInSe2 epitaxial layers grown by molecular beam epitaxy. Journal of Applied Physics, 1999, 86, 4354-4359.	1.1	23
121	Molecular beam epitaxial growth and characterization of CuInSe2 and CuGaSe2 for device applications. Journal of Crystal Growth, 2002, 237-239, 1993-1999.	0.7	23
122	Phase-change optical recording: Past, present, future. Thin Solid Films, 2007, 515, 7534-7537.	0.8	23
123	Reduction in crystallization time of Sb:Te films through addition of Bi. Applied Physics Letters, 2008, 92, .	1.5	23
124	Interfacial Alkali Diffusion Control in Chalcopyrite Thin-Film Solar Cells. ACS Applied Materials & Interfaces, 2014, 6, 14123-14130.	4.0	23
125	High-quality sputter-grown layered chalcogenide films for phase change memory applications and beyond. Journal Physics D: Applied Physics, 2020, 53, 284002.	1.3	23
126	Characterization of ZnO crystals by photoluminescence spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 872-875.	0.8	22

#	Article	IF	Citations
127	Photoluminescence characterization of excitonic centers in ZnO epitaxial films. Applied Physics Letters, 2005, 86, 221907.	1.5	22
128	Amorphous-to-Crystal Transition in Quasi-Two-Dimensional MoS₂: Implications for 2D Electronic Devices. ACS Applied Nano Materials, 2021, 4, 8834-8844.	2.4	22
129	Growth of CuGaSe2 film by molecular beam epitaxy. Microelectronics Journal, 1996, 27, 53-58.	1.1	21
130	Nucleation and growth of ZnO on sapphire substrates using molecular beam epitaxy. Journal of Crystal Growth, 2001, 227-228, 911-916.	0.7	21
131	An option for the surface science on Cu chalcopyrites: the selenium capping and decapping process. Surface Science, 2004, 557, 263-268.	0.8	21
132	Local structure of the SnTe topological crystalline insulator: Rhombohedral distortions emerging from the rocksalt phase. Physical Review B, 2014, 90, .	1.1	21
133	Ultrafast dynamics of the low frequency shear phonon in 1Tâ€²-MoTe2. Applied Physics Letters, 2020, 116, .	1.5	21
134	Ionâ€beam doping of GaAs with lowâ€energy (100 eV) C+using combined ionâ€beam and molecularâ€beam epitaxy. Journal of Applied Physics, 1995, 77, 146-152.	1.1	20
135	Thermal Conductivity Measurements of Sbâ€“Te Alloy Thin Films Using a Nanosecond Thermoreflectance Measurement System. Japanese Journal of Applied Physics, 2007, 46, 6863-6864.	0.8	20
136	A possible mechanism of ultrafast amorphization in phase-change memory alloys: an ion slingshot from the crystalline to amorphous position. Journal of Physics Condensed Matter, 2007, 19, 455209.	0.7	20
137	Effect of doping on global and local order in crystalline GeTe. Applied Physics Letters, 2011, 98, .	1.5	20
138	Observation of Exciton-Polariton Emissions from a ZnO Epitaxial Film on the a-Face of Sapphire Grown by Radical-Source Molecular-Beam-Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L935-L937.	0.8	19
139	A XANES Study of Cu Valency in Cu-Doped Epitaxial ZnO. Physica Status Solidi (B): Basic Research, 2002, 229, 849-852.	0.7	19
140	Picosecond strain dynamics in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ge</mml:mi><mml:mn>1</mml:mn></mml:msub></mml:mrow></mml:math>Sb<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Te<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>4</mml:mn></mml:msub></mml:math> by time-resolved x-ray diffraction. Physical Review B, 2014, 90, .	1.1	19
141	Compositional tuning in sputter-grown highly-oriented Biâ€“Te films and their optical and electronic structures. Nanoscale, 2017, 9, 15115-15121.	2.8	19
142	The strain energy density of cubic epitaxial layers. Journal of Crystal Growth, 1996, 160, 406-412.	0.7	18
143	In situ deposition rate monitoring during the three-stage-growth process of Cu(In,Ga)Se2 absorber films. Thin Solid Films, 2003, 431-432, 16-21.	0.8	18
144	Local atomic order of crystalline Ge<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>8</mml:mn></mml:msub></mml:math>Sb<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Te<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mml:	1.1	18

#	Article	IF	Citations
145	Recrystallization of an amorphized epitaxial phase-change alloy: A phoenix arising from the ashes. Applied Physics Letters, 2012, 101, 061903.	1.5	18
146	Strain engineering of atomic and electronic structures of few-monolayer-thick GaN. Physical Review Materials, 2017, 1, .	0.9	18
147	Static analysis of off-axis crystal film growth onto a lattice-mismatched substrate. Applied Physics Letters, 2001, 79, 608-610.	1.5	17
148	Manipulating the Bulk Band Structure of Artificially Constructed van der Waals Chalcogenide Heterostructures. ACS Applied Materials & Interfaces, 2017, 9, 23918-23925.	4.0	17
149	Zener Tunneling Breakdown in Phase-Change Materials Revealed by Intense Terahertz Pulses. Physical Review Letters, 2018, 121, 165702.	2.9	17
150	Low energy (100 eV) C+ion doping into GaAs using combined ion beam and molecular beam epitaxial technology. Applied Physics Letters, 1993, 63, 1951-1953.	1.5	16
151	Dimensional transformation of chemical bonding during crystallization in a layered chalcogenide material. Scientific Reports, 2021, 11, 4782.	1.6	16
152	Effects of annealing on CuInSe2 films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1997, 49, 319-326.	3.0	15
153	Growth of LiNbO 3 epitaxial films by oxygen radical-assisted laser molecular beam epitaxy. Applied Physics A: Materials Science and Processing, 1999, 69, S679-S681.	1.1	15
154	Soft X-ray XANES of N in ZnO:N â€“ Why is doping so difficult?. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 75-78.	0.6	15
155	Characteristics of nanostructured Ag films by the reduction of sputtered AgOxthin films. Nanotechnology, 2006, 17, 79-82.	1.3	15
156	CIGS thin films, solar cells, and submodules fabricated using a rf-plasma cracked Se-radical beam source. Thin Solid Films, 2011, 519, 7216-7220.	0.8	15
157	Polarization dependent optical control of atomic arrangement in multilayer Ge-Sb-Te phase change materials. Applied Physics Letters, 2012, 101, 232101.	1.5	15
158	A reconsideration of the thermodynamics of phaseâ€change switching. Physica Status Solidi (B): Basic Research, 2012, 249, 1932-1938.	0.7	15
159	Athermal amorphization of crystallized chalcogenide glasses and phase-change alloys. Physica Status Solidi (B): Basic Research, 2014, 251, 1297-1308.	0.7	15
160	Epitaxial growth of Si by ArF laserâ€excited supersonic free jets of Si2H6. Applied Physics Letters, 1993, 63, 3473-3475.	1.5	14
161	pâ€Type conductivity of GeTe: The role of loneâ€pair electrons. Physica Status Solidi (B): Basic Research, 2012, 249, 1902-1906.	0.7	14
162	Coherent phonon study of (GeTe)l(Sb2Te3)m interfacial phase change memory materials. Applied Physics Letters, 2014, 105, 151902.	1.5	14

#	Article	IF	Citations
163	Local structure of the crystalline and amorphous states of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ga</mml:mi><mml:mn>2</mml:mn></mml: alloy without resonant bonding: A combined x-ray absorption andab initiostudy. Physical Review B, 2017, 95, .	1.1	14
164	Highâ€Speed Bipolar Switching of Sputtered Geâ€“Te/Sbâ€“Te Superlattice iPCM with Enhanced Cyclability. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900105.	1.2	14
165	Lithium-Doping Effects in Cu(In,Ga)Se₂ Thin-Film and Photovoltaic Properties. ACS Applied Materials & Interfaces, 2020, 12, 25058-25065.	4.0	14
166	Observation of diamond crystallites in thin films prepared by laser ablation of hard fullerene-based carbon. Journal Physics D: Applied Physics, 1996, 29, 929-933.	1.3	13
167	InGaN-based light-emitting diodes fabricated with transparent Ga-doped ZnO as ohmicp-contact. Physica Status Solidi A, 2004, 201, 2704-2707.	1.7	13
168	Sub-Nanosecond Time-Resolved Structural Measurements of the Phase-Change Alloy Ge2Sb2Te5. Japanese Journal of Applied Physics, 2007, 46, 3711-3714.	0.8	13
169	Proposal of a grating-based optical reflection switch using phase change materials. Optics Express, 2009, 17, 16947.	1.7	13
170	Amorphous InSb: Longer bonds yet higher density. Journal of Applied Physics, 2010, 108, 023506.	1.1	13
171	Pressure-induced structural transitions in phase-change materials based on Ge-free Sb-Te alloys. Physical Review B, 2011, 83, .	1.1	13
172	Enhanced Sb2S3 crystallisation by electric field induced silver doping. Thin Solid Films, 2016, 616, 80-85.	0.8	13
173	Role of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Cu</mml:mi></mml:math> -Deficient Interface in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Cu</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq1 1 0.784314 rg	1.5	13
174	Determination of the lattice constants of epitaxial layers. Journal of Crystal Growth, 1995, 154, 401-409.	0.7	12
175	Temperature dependence of photoacoustic spectra in CuInSe2 thin films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1998, 50, 127-132.	3.0	12
176	Effects of Sodium on CuIn3Se5 Thin Films. Japanese Journal of Applied Physics, 1999, 38, L899-L901.	0.8	12
177	Electron beam probe quantization of compound composition: surface phases and surface roughness. Thin Solid Films, 2003, 431-432, 277-283.	0.8	12
178	Adjusting the sodium diffusion into CuInGaSe2 absorbers by preheating of Mo/SLG substrates. Journal of Physics and Chemistry of Solids, 2003, 64, 1877-1880.	1.9	12
179	Local structure of amorphous Geï£¿Sbï£¿Te alloys: Ge umbrella flip vs. DFT simulations. Physica Status Solidi (B): Basic Research, 2009, 246, 1826-1830.	0.7	12
180	Recent developments concerning the sputter growth of chalcogenide-based layered phase-change materials. Materials Science in Semiconductor Processing, 2021, 135, 106079.	1.9	12

#	Article	IF	Citations
181	Second-harmonic generation from CuInSe/sub 2/ thin films: influence of the substrate-epilayer lattice mismatch. IEEE Journal of Quantum Electronics, 1997, 33, 1294-1298.	1.0	11
182	Temperature variation of nonradiative carrier recombination processes in high-quality CuGaSe2 thin films grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 259-261.	1.5	11
183	Control of the thin film properties of Cu(In,Ga)Se2 using water vapor introduction during growth. Journal of Applied Physics, 2006, 100, 096106.	1.1	11
184	Thermal conductivity measurements of low-k films using thermoreflectance phenomenon. Microelectronic Engineering, 2008, 85, 796-799.	1.1	11
185	Study of band inversion in the Pb_xSn_{1â^'x}Te class of topological crystalline insulators using x-ray absorption spectroscopy. Journal of Physics Condensed Matter, 2014, 26, 475502.	0.7	11
186	Si-Doping Effects in Cu(In,Ga)Se₂ Thin Films and Applications for Simplified Structure High-Efficiency Solar Cells. ACS Applied Materials & Interfaces, 2017, 9, 31119-31128.	4.0	11
187	Coherent Dirac plasmons in topological insulators. Physical Review B, 2018, 97, .	1.1	11
188	Understanding the fast phase-change mechanism of tetrahedrally bonded <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Cu</mml:mi><mml:mn>2</mml:mn></mml:msub><mml: : Comprehensive analyses of electronic structure and transport phenomena. Physical Review B, 2018, 97, .	1.1	11
189	The importance of contacts in Cu2GeTe3 phase change memory devices. Journal of Applied Physics, 2020, 128, .	1.1	11
190	Molecular dynamics and quasidynamics simulations of low-energy ion/surface interactions leading to decreased epitaxial temperatures and increased dopant incorporation probabilities during Si MBE. Journal of Crystal Growth, 1991, 111, 870-875.	0.7	10
191	A Reversible Change of Reflected Light Intensity between Molten and Solidified Geâ€“Sbâ€“Te Alloy. Japanese Journal of Applied Physics, 2007, 46, L868-L870.	0.8	10
192	Interface oxygen and heat sensitivity of Cu(In,Ga)Se2 and CuGaSe2 solar cells. Applied Physics Letters, 2016, 108, 203902.	1.5	10
193	A cascading nonlinear magneto-optical effect in topological insulators. Scientific Reports, 2018, 8, 3908.	1.6	10
194	Insights into the physics and chemistry of chalcogenides obtained from x-ray absorption spectroscopy. Semiconductor Science and Technology, 2017, 32, 123003.	1.0	10
195	Photoâ€Induced Tellurium Segregation in MoTe₂. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	1.2	10
196	Determination of the valence electronic structure of condensed trimethylaluminum by photoelectron spectroscopy and molecularâ€orbital calculations. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 3115-3119.	0.9	9
197	Amorphization Processes in Ion Implanted Si: Temperature Dependence. Japanese Journal of Applied Physics, 1991, 30, 3617-3620.	0.8	9
198	Control of intrinsic defects in molecular beam epitaxy grown CuInSe2. Journal of Crystal Growth, 1999, 201-202, 1061-1064.	0.7	9

#	Article	IF	Citations
199	Effects of low temperature buffer layer treatments on the growth of high quality ZnO films. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 888-891.	0.8	9
200	Local structure of epitaxial GeTe and Ge₂Sb₂Te₅ films grown on InAs and Si substrates with (100) and (111) orientations: An x-ray absorption near-edge structure study. Journal of Applied Physics, 2015, 117, 125308.	1.1	9
201	Anisotropic lattice response induced by a linearly-polarized femtosecond optical pulse excitation in interfacial phase change memory material. Scientific Reports, 2016, 6, 19758.	1.6	9
202	Soft X-ray Absorption Spectroscopy Probes OHÂ·Â·Â·Ï€ Interactions in Epoxy-Based Polymers. Journal of Physical Chemistry C, 2020, 124, 9622-9627.	1.5	9
203	Phase control of sputter-grown large-area MoTe2 films by preferential sublimation of Te: amorphous, 1Tâ€² and 2H phases. Journal of Materials Chemistry C, 2022, 10, 10627-10635.	2.7	9
204	Selective Dissociative Ionization of SiH4, Si2H6and Si3H8by Electron Impact in Supersonic Free Jets. Japanese Journal of Applied Physics, 1993, 32, L879-L882.	0.8	8
205	Siâ€Ðoped Cu(In,Ga)Se₂ Photovoltaic Devices with Energy Conversion Efficiencies Exceeding 16.5% without a Buffer Layer. Advanced Energy Materials, 2018, 8, 1702391.	10.2	8
206	Terahertz generation measurements of multilayered GeTeâ€“Sb₂Te₃ phase change materials. Optics Letters, 2019, 44, 1355.	1.7	8
207	Molecular Dynamics Simulations of Low-Energy Ion/Surface Interactions During Vapor Phase Crystal Growth: 10 eV Si Incident on Si(001)2Ã—1. Materials Research Society Symposia Proceedings, 1989, 157, 259.	0.1	7
208	Photoreflectance and Photoluminescence of Exciton-Polaritons in a ZnO Epilayer Grown on the a-Face of Sapphire by Radical-Source Molecular-Beam Epitaxy. Physica Status Solidi A, 2002, 192, 171-176.	1.7	7
209	High-pressure induced structural changes in metastable Ge2Sb2Te5 thin films: An X-ray absorption study. Nuclear Instruments & Methods in Physics Research B, 2005, 238, 160-162.	0.6	7
210	Athermal component of amorphisation in phase-change alloys and chalcogenide glasses. Journal of Non-Crystalline Solids, 2012, 358, 2398-2401.	1.5	7
211	Hard x-ray photoelectron spectroscopy study of Ge2Sb2Te5; as-deposited amorphous, crystalline, and laser-reamorphized. Applied Physics Letters, 2014, 104, 061909.	1.5	7
212	Resistive switching characteristics of interfacial phase-change memory at elevated temperature. Japanese Journal of Applied Physics, 2018, 57, 04FE06.	0.8	7
213	Systematic materials design for phase-change memory with small density changes for high-endurance non-volatile memory applications. Applied Physics Express, 2019, 12, 051008.	1.1	7
214	Chalcogenide Materials Engineering for Phaseâ€Change Memory and Future Electronics Applications: From Sbâ€“Te to Biâ€“Te. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000414.	1.2	7
215	In-situRaman Scattering Spectroscopy for a Super Resolution Optical Disk during Readout. Applied Physics Express, 0, 2, 082402.	1.1	7
216	Improved Ordering of Quasi-Two-Dimensional MoS₂ via an Amorphous-to-Crystal Transition Initiated from Amorphous Sulfur-Rich MoS_{2+x}. Crystal Growth and Design, 2022, 22, 3072-3079.	1.4	7

#	Article	IF	Citations
217	Vacuum ultraviolet photolysis of supersonic free jets of SiH4. Applied Surface Science, 1994, 79-80, 476-480.	3.1	6
218	Evidence of crystalline diamond in thin films prepared by laser ablation of hard fullereneâ€based carbon. Journal of Applied Physics, 1996, 80, 1182-1185.	1.1	6
219	Electron Probe Microanalysis of Second Phases via Acceleration Voltage Dependence. Japanese Journal of Applied Physics, 1999, 38, L96-L98.	0.8	6
220	Deposition of Ge1-xCxAlloy on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxial Method. Japanese Journal of Applied Physics, 1999, 38, 3459-3465.	0.8	6
221	Local Structure of AgOxThin Layers Generating Optical Near Field: an X-Ray Absorption Fine Structure Study. Japanese Journal of Applied Physics, 2003, 42, 1022-1025.	0.8	6
222	Structural changes of CIGS during deposition investigated by spectroscopic light scattering: A study on Ga concentration and Se pressure. Solar Energy Materials and Solar Cells, 2006, 90, 3377-3384.	3.0	6
223	Comment on â€œNew Structural Picture of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Ge</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Sb</mml:mi><mml:mn Alloyâ€• Physical Review Letters, 2012, 108, 239603; author reply 239602.	7.9	6
224	Low temperature photoluminescence from GaAs impinged by mass-separated low-energy C⁺ ion beams during molecular beam epitaxy. Materials Research Society Symposia Proceedings, 1993, 316, 1029.	0.1	5
225	The Strain Energy Densities of Hexagonal and Tetragonal Epitaxial Media. Japanese Journal of Applied Physics, 1995, 34, L1616-L1619.	0.8	5
226	Natural ordering of ZnO1â^'xSex grown by radical source MBE. Journal of Crystal Growth, 2003, 251, 633-637.	0.7	5
227	The chemical environment about Cd atoms in Cd chemical bath treated CuInSe2 and CuGaSe2. Journal of Physics and Chemistry of Solids, 2003, 64, 1733-1735.	1.9	5
228	Determination of crystallographic polarity of ZnO bulk crystals and epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1018-1021.	0.8	5
229	Read-out enhancement of super-resolution near-field structures using the pit shape. Nanotechnology, 2006, 17, 1481-1483.	1.3	5
230	Crystallization of Bi Doped Sb₈Te₂. Japanese Journal of Applied Physics, 2009, 48, 03A062.	0.8	5
231	Thermal conductivity of low-k films of varying porosity and direct measurements on silicon substrate. Microelectronic Engineering, 2009, 86, 1009-1012.	1.1	5
232	Disorder in order: A study of local and global order in Geâ€rich Geï£¿Sbï£¿Te alloys. Physica Status Solidi (B): Basic Research, 2012, 249, 1919-1924.	0.7	5
233	Amorphous phase of GeTeâ€based phaseâ€change memory alloys: Polyvalency of Geï£¿Te bonding and polyamorphism. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1031-1035.	0.8	5
234	Detection of N-Te bonds in the as-deposited amorphous nitrogen-doped GeTe-based phase change alloys using N K-edge XANES spectroscopy and their impact on crystallization. Journal of Alloys and Compounds, 2017, 704, 254-259.	2.8	5

#	Article	IF	Citations
235	A comparative study of the effects of sputtering deposition conditions for ZnO surface electrode layers on Cu(In,Ga)Se2 and CuGaSe2 solar cells. Thin Solid Films, 2017, 633, 49-54.	0.8	5
236	(Invited) Sputter Growth of Chalcogenide Superlattice Films for Future Phase Change Memory Applications. ECS Transactions, 2018, 86, 49-54.	0.3	5
237	Chalcogenide van der Waals superlattices: a case example of interfacial phase-change memory. Pure and Applied Chemistry, 2019, 91, 1777-1786.	0.9	5
238	Polycrystalline CuGaSe2 thin film growth and photovoltaic devices fabricated on alkali-free and alkali-containing substrates. Journal of Crystal Growth, 2020, 532, 125407.	0.7	5
239	Dielectric Relaxation and Charge Transfer in Amorphous MoS₂ Thin Films. Physica Status Solidi (B): Basic Research, 2020, 257, 2000114.	0.7	5
240	Dielectric relaxation in amorphous and crystalline Sb2Te3 thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 14072-14078.	1.1	5
241	Fermi surface dependence of the hall coefficient in quasi-2D molecular conductors. Synthetic Metals, 1995, 70, 1001-1004.	2.1	4
242	Effect of strain and temperature on anomalously large interdiffusion in InAsP/InP heterostructures. Applied Physics Letters, 1997, 70, 3410-3412.	1.5	4
243	Effects of strain on the growth and properties of CuInSe2 epitaxial films. Journal of Crystal Growth, 1997, 175-176, 1051-1056.	0.7	4
244	Observation of Interdiffusion in ZnO/CuInSe2 Heterostructures and its Effect on Film Properties. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	4
245	High-Quality Transparent Conducting Oxide Films Deposited by a Novel Ion Plating Technique. Materials Research Society Symposia Proceedings, 2003, 763, 741.	0.1	4
246	Bandgap Engineering of ZnO Transparent Conducting Films. Materials Research Society Symposia Proceedings, 2003, 763, 721.	0.1	4
247	Enhancement of coherent phonon amplitude in phase-change materials by near-infrared laser irradiation. Applied Physics Letters, 2017, 111, .	1.5	4
248	Topological Phase Buried in a Chalcogenide Superlattice Monitored by Helicity-Dependent Kerr Measurement. ACS Applied Materials & Interfaces, 2018, 10, 26781-26786.	4.0	4
249	Understanding the low resistivity of the amorphous phase of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Cr</mml:mi><mml:mn>2</mml:mn></mml:mn></mml: phase-change material: Experimental evidence for the key role of Cr clusters. Physical Review Materials, 2021, 5, .	0.9	4
250	Evolution of the local structure surrounding nitrogen atoms upon the amorphous to crystalline phase transition in nitrogen-doped Cr2Ge2Te6 phase-change material. Applied Surface Science, 2021, 556, 149760.	3.1	4
251	Phase-Change Memory Materials. Springer Handbooks, 2017, , 1-1.	0.3	4
252	Strain-Induced Diffusion in Heteroepitaxially Grown CuInSe₂ on GaAs Substrates. Materials Research Society Symposia Proceedings, 1995, 399, 549.	0.1	3

#	Article	IF	Citations
253	Photoluminescence investigation of Hg acceptor in GaAs. Applied Physics Letters, 1995, 67, 1465-1467.	1.5	3
254	The Effects of Kcn Etching on Cu-Rich Epitaxial CuInSe₂ Thin Films. Materials Research Society Symposia Proceedings, 1996, 426, 213.	0.1	3
255	Translational Phase Domains in the Cation Sublattice of Chalcopyrite Compounds. Japanese Journal of Applied Physics, 1996, 35, L843-L845.	0.8	3
256	Piezoelectric photoacoustic spectra of CuInSe2 thin film grown by molecular beam epitaxy. Thin Solid Films, 1999, 343-344, 591-593.	0.8	3
257	Control of Optical and Electrical Properties of ZnO Films for Photovoltaic Applications. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	3
258	Point Defect Changes in CuGaSe2 Induced by Gas Annealing. Materials Research Society Symposia Proceedings, 2003, 763, 5171.	0.1	3
259	Improvement in the aspect ratio of fabricated minute dots by the volume change thermal lithography technique. Microelectronic Engineering, 2005, 78-79, 359-363.	1.1	3
260	Development of a geometrical evaluation apparatus for ultrahigh 100 GB optical disk masters. Review of Scientific Instruments, 2005, 76, 083706.	0.6	3
261	Localized Light Focusing and Super Resolution Readout via Chalcogenide Thin Film. Materials Research Society Symposia Proceedings, 2006, 918, 1.	0.1	3
262	Epitaxial Phase Change Materials: Growth and Switching of Ge₂Sb₂Te₅ on GaSb(001). Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	3
263	Stress Limited Scaling of Ge₂Sb₂Te₅. Materials Research Society Symposia Proceedings, 2010, 1251, 2.	0.1	3
264	Laser-driven switching dynamics in phase change materials investigated by time-resolved X-ray absorption spectroscopy. Phase Transitions, 2015, 88, 82-89.	0.6	3
265	Pressure-Induced Phase Transitions in GeTe-Rich Geâ€“Sbâ€“Te Alloys across the Rhombohedral-to-Cubic Transitions. Inorganic Chemistry, 2017, 56, 7687-7693.	1.9	3
266	Structural Metastability in Chalcogenide Semiconductors: The Role of Chemical Bonding. Physica Status Solidi (B): Basic Research, 2020, 257, 2000138.	0.7	3
267	Electric Fields and Interfacial Phaseâ€Change Memory Structures. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000412.	1.2	3
268	Crystallization of Ge2Sb2Te5 under high hydrostatic pressures: Differences in nanoscale atomic ordering in as-deposited and pressure-induced amorphous phases. Journal of Alloys and Compounds, 2021, 874, 159980.	2.8	3
269	Polymorphism of CdTe in the Fewâ€Monolayer Limit. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100358.	1.2	3
270	Control of Intrinsic Defects in CuInSe₂ Films for Device Applications. Japanese Journal of Applied Physics, 2000, 39, 149.	0.8	3

#	Article	IF	Citations
271	Twin formation in Cu-Ga-Se films grown by molecular beam epitaxy under Ga-excess conditions. Japanese Journal of Applied Physics, 2000, 39, 200.	0.8	3
272	Electronic Structure of Adsorbed Trimethylaluminum on Clean Si(100) Surfaces. Materials Research Society Symposia Proceedings, 1988, 131, 345.	0.1	2
273	Optical Characterization of 100 eV C+ Ion Doped GaAs. Materials Research Society Symposia Proceedings, 1993, 300, 357.	0.1	2
274	Determination of the composition of strained tetragonal epilayers. Applied Physics Letters, 1996, 69, 761-763.	1.5	2
275	Cation sublattice stacking faults in Cu-rich chalcopyrite CuInSe₂. Journal of Materials Research, 1996, 11, 1398-1402.	1.2	2
276	Significant Compositional Changes and Formation of a Ga-O Phase after Oxygen-annealing of Ga-rich CuGaSe₂ Films. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	2
277	Optical properties of high-quality CuGaSe2 epitaxial layers examined by piezoelectric photoacoustic spectroscopy. Solar Energy Materials and Solar Cells, 2001, 67, 173-178.	3.0	2
278	Far-infrared optical conductivity of YBCO single crystal thin films from transmission and reflection spectra. Journal of Physics and Chemistry of Solids, 2001, 62, 253-256.	1.9	2
279	Structural changes of CuGaSe2 films during the three-stage process observed by spectroscopic light scattering. Thin Solid Films, 2005, 480-481, 367-372.	0.8	2
280	Understanding Structural Changes in Phase Change Memory Alloys. Materials Research Society Symposia Proceedings, 2006, 918, 1.	0.1	2
281	Preparation of Cu(In1-xGax)Se2 Thin Films and Solar Cells Using a Se-radical Beam Source. Materials Research Society Symposia Proceedings, 2007, 1012, 1.	0.1	2
282	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. AIP Conference Proceedings, 2007, , .	0.3	2
283	Short and Long-Range Order in Phase Change Materials. , 2009, , 149-174.		2
284	The first principle computer simulation and real device characteristics of superlattice phase-change memory. , 2010, , .		2
285	Ultrafast optical manipulation of atomic motion in multilayer Ge-Sb-Te phase change materials. EPJ Web of Conferences, 2013, 41, 03007.	0.1	2
286	Doping of ZnO nanowires using phosphorus diffusion from a spin-on doped glass source. Journal of Applied Physics, 2014, 115, 194302.	1.1	2
287	Anomalous Phase Change in [(GeTe)2/(Sb2Te3)]20 Superlattice Observed by Coherent Phonon Spectroscopy. Springer Proceedings in Physics, 2015, , 199-201.	0.1	2
288	Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/Sb2Te3 Superlattices. MRS Advances, 2018, 3, 3413-3418.	0.5	2

#	Article	IF	Citations
289	Photon energy dependence of Kerr rotation in GeTe/Sb₂Te₃ chalcogenide superlattices. Journal of Physics Condensed Matter, 2019, 31, 415502.	0.7	2
290	Investigation of the oxidation process in GeTe-based phase change alloy using Ge K-edge XANES spectroscopy. Pure and Applied Chemistry, 2019, 91, 1769-1775.	0.9	2
291	Ultrafast scattering dynamics of coherent phonons in Bi_{1â^'x}Sb_x in the Weyl semimetal phase. New Journal of Physics, 2021, 23, 023034.	1.2	2
292	Crystalline Sb 2 Te 3 : Side Surfaces and Disappearance of Dirac Cones. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000418.	1.2	2
293	A High Resolution X-ray Diffraction and TEM Study of the CuxSe Surface Phase of Cu-rich CuInSe2. Japanese Journal of Applied Physics, 2000, 39, 189.	0.8	2
294	The formation of a one-dimensional van der Waals selenium crystal from the three-dimensional amorphous phase: A spectroscopic signature of van der Waals bonding. Applied Physics Letters, 2022, 120, 033103.	1.5	2
295	Effects of Hyperthermal Carbon Subimplantation Doping on the Raman Spectra of Gaas. Materials Research Society Symposia Proceedings, 1993, 316, 1011.	0.1	1
296	Growth of Ge1-xCx Alloys on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxy Method. Materials Research Society Symposia Proceedings, 1996, 438, 393.	0.1	1
297	Estimation and Correction Procedure for the Effects of Surface Roughness on Electron Probe Microanalysis. Japanese Journal of Applied Physics, 2003, 42, 5811-5812.	0.8	1
298	Nanometer-scale mechanism of phase-change optical recording as revealed by XAFS. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 69-74.	0.6	1
299	X-ray absorption spectroscopy of high-k gate dielectric insulating layers for next-generation semiconductor devices as measured by superconducting detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2006, 559, 731-733.	0.7	1
300	What Makes Phase-Change Chalcogenide Alloys Materials of Choice for Optical Data Storage. Materials Research Society Symposia Proceedings, 2006, 918, 5.	0.1	1
301	Optically Induced Sub-Wavelength Transient Apertures in Sb-Te Based Films. Materials Research Society Symposia Proceedings, 2011, 1338, 32001.	0.1	1
302	Nanometer Resolution XANES Imaging of in situ switched individual PC-RAM devices. Materials Research Society Symposia Proceedings, 2013, 1563, 1.	0.1	1
303	Coherent gigahertz phonons in Ge2Sb2Te5phase-change materials. Journal of Physics Condensed Matter, 2015, 27, 485402.	0.7	1
304	Effects of electric and magnetic fields on the resistive switching operation of iPCM. Applied Physics Letters, 2020, 116, 201903.	1.5	1
305	Dielectric relaxation in the GeSb2Te4 phase-change material. AIP Conference Proceedings, 2020, , .	0.3	1
306	Bond-Selective Excitation and Following Displacement of Ge Atoms in GeTe/Sb2Te3Superlattice. Acta Physica Polonica A, 2012, 121, 336-339.	0.2	1

#	Article	IF	Citations
307	Disappearance of the surface Cu-Se second phase during post-growth annealing of CuInSe₂ epitaxial films grown under excess Cu-flux conditions. Japanese Journal of Applied Physics, 2000, 39, 205.	0.8	1
308	Defect Structure of Cu-Rich and In-Rich Chalcopyrite CuInSe2 Films Grown on GaAS. Materials Research Society Symposia Proceedings, 1995, 399, 467.	0.1	0
309	Growth of Ge1â^'xCx, Alloys on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxy Method. Materials Research Society Symposia Proceedings, 1996, 439, 233.	0.1	0
310	Structural and Surface Morphology Changes in CuInSe₂ Thin Films as a Function of Cu/In Ratio. Materials Research Society Symposia Proceedings, 1996, 441, 9.	0.1	0
311	Piezoelectric Photoacoustic Spectra In CuGaSe2 Thin Films Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1997, 485, 151.	0.1	0
312	In-Situ Surface Composition Measurements of CuGaSe2 Thin Films. Materials Research Society Symposia Proceedings, 1997, 485, 145.	0.1	0
313	Formalistic description of multislice calculation method. , 1998, 40, 152-161.		0
314	Far-infrared optical conductivity of YBa2Cu3O7 â^' Ï‡ thin films. Physica C: Superconductivity and Its Applications, 2000, 341-348, 2197-2200.	0.6	0
315	Natural ordering of ZnO/sub 1-x/Se/sub x/ grown by radical source MBE. , 0, , .		0
316	Local structure of AgO/sub x/ thin layers generating optical near-field. , 0, , .		0
317	Thermal processing induced structural changes in ZnO films grown on (11&2macr;0) sapphire substrates using molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 868-871.	0.8	0
318	XAFS Observations of Initial Growth of 0001 ZnO on Sapphire Substrates. Physica Scripta, 2005, , 523.	1.2	0
319	An XAFS Study of Amorphous Crystalline Phase Transitions along the GeTe-Sb2Te3 Pseudobinary Tie Line. , 2005, , WC4.		0
320	Laser-induced Ge Atom Switching as aKey to Understanding Phase-change Optical Media. , 0, , .		0
321	Photoluminescence recombination centers in ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1026-1029.	0.8	0
322	X-Ray Fluorescence Holographic Study on a Single-Crystal Thin Film of a Rewritable Optical Media. AIP Conference Proceedings, 2007, , .	0.3	0
323	Formation of two-dimensional electron gas and enhancement of electron mobility by Zn polar ZnMgO/ZnO heterostructures. , 2007, 6474, 78.		0
324	Large Optical Transitions in Rewritable Digital Versatile Discs: An Interlayer Atomic Zipper in a SbTe Alloy. Materials Research Society Symposia Proceedings, 2008, 1072, 1.	0.1	0

#	Article	IF	Citations
325	The role of vacancies in the pressure amorphisation phenomenon observed in Ge-Sb-Te phase change alloys. Materials Research Society Symposia Proceedings, 2010, 1251, 10.	0.1	0
326	Characterization of CIGS thin films and solar cells grown with a plasma-cracked Se source. , 2011, , .		0
327	Nanometer Resolution XANES Imaging of Individual PC-RAM Devices. Materials Research Society Symposia Proceedings, 2012, 1431, 26.	0.1	0
328	Publisher's Note: Crystalline GeTe-based phase-change alloys: Disorder in order [Phys. Rev. B86, 045212 (2012)]. Physical Review B, 2012, 86, .	1.1	0
329	Anomalous phase change process in [(GeTe)2/(Sb2Te3)]20 superlattice observed by coherent phonon spectroscopy. , 2014, , .		0
330	Allâ€Optical Detection of Periodic Structure of Chalcogenide Superlattice Using Coherent Folded Acoustic Phonons. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800246.	1.2	0
331	Switching of the Optical Properties of Ge2Sb2Te5 Phase Change Material in the Terahertz Frequency Region. , 2019, , .		0
332	Transient Fano Resonance in topological insulators observed by coherent phonon spectroscopy. EPJ Web of Conferences, 2019, 205, 04021.	0.1	0
333	Polarization Processes in Thin Layers of Amorphous MoS2 Obtained by RF Magnetron Sputtering. Semiconductors, 2020, 54, 558-562.	0.2	0
334	Structural and Dielectric Study of Thin Amorphous Layers of the Geâ€“Sbâ€“Te System Prepared by RF Magnetron Sputtering. Semiconductors, 2020, 54, 201-204.	0.2	0
335	Phase Change Materials for Optical Disc and Display Applications. , 2021, , 681-711.		0
336	Phase-Change Alloys: Structural Aspects. , 2021, , 323-339.		0
337	Exciton structures of single- and polycrystalline CuInSe2and CuGaSe2. Japanese Journal of Applied Physics, 2000, 39, 326.	0.8	0
338	Structure in the local environment of Zn2+ion in the anti-termination protein ofBacillus subtilis. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C110-C111.	0.3	0
339	Ultrafast Lattice Dynamics of Phase-change Materials Monitored by a Pump-pump-probe Technique. , 2014, , .		0
340	Photoluminescence investigation of a new emission formed in Mn+ implanted ultra-pure GaAs grown by MBE. , 1994, , 373-376.		0
341	Dielectric Relaxation and Photo-electromotive Force in Ge-Sb-Te/Si Structures. , 2020, , .		0